

1MBH10D-120

1200V / 10A Molded Package

Features

- Small molded package
- Low power loss
- $\boldsymbol{\cdot}$ Soft switching with low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)
- Comprehensive line-up

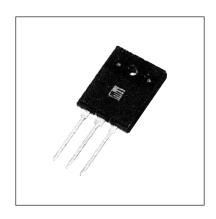
Applications

- Inverter for Motor drive
- · AC and DC Servo drive amplifier
- Uninterruptible power supply

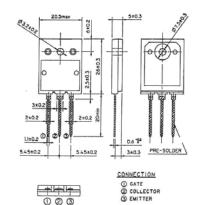
Maximum Ratings and Characteristics

• Absolute Maximum Ratings (Tc=25°C)

Items			Symbols	Ratings	Units
Collector-Emitter Voltage			VCES	1200	V
Gate-Emitter Voltage			VGES	±20	V
	DC	TC=25°C	IC25	18	A
Collector Current		TC=105℃	IC110	10	A
	1ms	TC=25°C	lcp	48	A
IGBT Max. Power Dissipation			Pc	155	W
FWD Max. Power Dissipation			Pc	105	W
Operating Temperature			Tj	+150	C
Storage Temperature			Tstg	-40 to +150	C°
Mounting Screw Torque			-	70	N∙cm



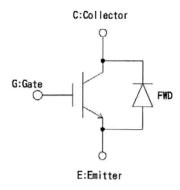
Outline drawings, mm



• Electrical Characteristics (at Tc=25°C unless otherwise specified)

Items		Cumhala	Characteristics			Conditions	Units
		Symbols	min.	typ.	max.	Conditions	Units
Zero gate voltage Collector Current		ICES	-	—	1.0	$V_{GE} = 0V, V_{CE} = 1200V$	mA
Gate-Emitter leakage Current		Iges	-	—	20	$V_{CE} = 0V, V_{GE} = \pm 20V$	μA
Gate-Emitter Threshold Voltage		V _{GE} (th)	5.5	_	8.5	Vce = 20V, Ic = 10mA	V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	-	—	3.5	$V_{GE} = 15V$, $Ic = 10A$	V
Input capacitance		Cies	-	1200	-	V _{GE} = 0V	pF
Output capacitance		Coes	-	250	-	Vce = 10V	
Reverse transfer	capacitance	Cres	-	80	-	f = 1MHz	
Switching Time	Turn-on time	ton	-	—	1.2	Vcc = 600V	μs
		tr	-	_	0.6	Ic = 10A V _{GE} = ±15V	
	Turn-off time	toff	-	_	1.5	$R_G = 160\Omega$	
		tf	-	-	0.5	(Half Bridge)	
	Turn-on time	ton	-	0.16	-	Vcc = 600V	
		tr	-	0.11	-	Ic = 10A V _{GE} = +15V	
	Turn-off time	toff	-	0.30	-	$R_G = 16\Omega$	
		tf	-	_	0.50	(Half Bridge)	
FWD forward voltage drop		VF	-	-	3.0	IF = 10A	V
Reverse recovery time ti		trr	_	_	0.35	$I_F = 10A, V_{GE} = -10V$ VR = 200V di/dt = 100A/µs	μs

Equivalent circuit

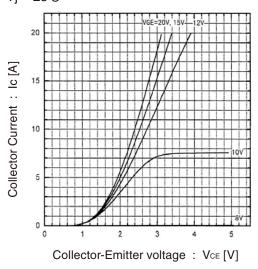


• Thermal resistance Characteristics

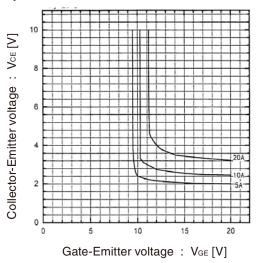
Items	Symbols	Characteristics			Conditions	Units
Items		min.	typ.	max.	Conditions	Units
They well registered	Rth(j-c)	-	-	0.80	IGBT	°C/W
Thermal resistance	Rth(j-c)	-	-	1.19	FWD	

Characteristics

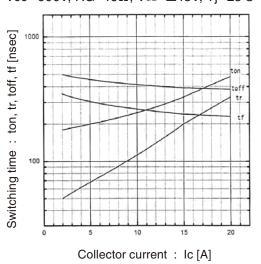
Collector current vs. Collector-Emitter voltage $Tj = 25^{\circ}C$



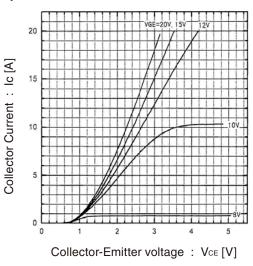
Collector-Emitter voltage vs. Gate-Emitter Voltage Tj = $25^{\circ}C$



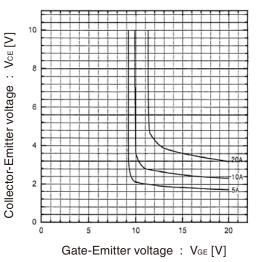
Switching time vs. Collector current Vcc=600V, RG=16 Ω , V_{GE}=±15V, Tj=25°C



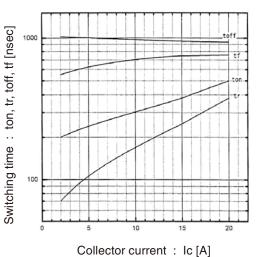
Collector current vs. Collector-Emitter voltage $Tj = 125^{\circ}C$



Collector-Emitter voltage vs. Gate-Emitter Voltage Tj = $125^{\circ}C$

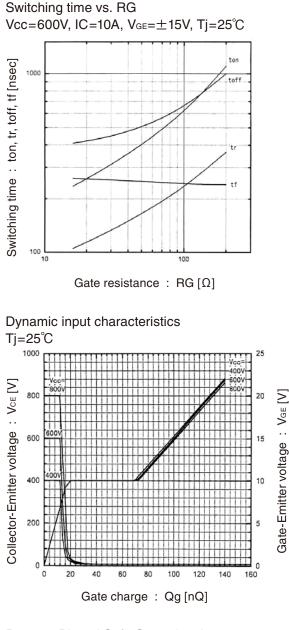


Switching time vs. Collector current Vcc=600V, RG=16 Ω , V_{GE}= \pm 15V, Tj=125°C

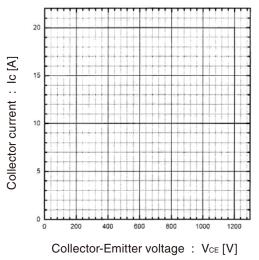


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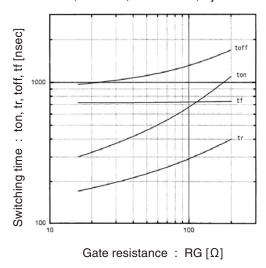
Characteristics



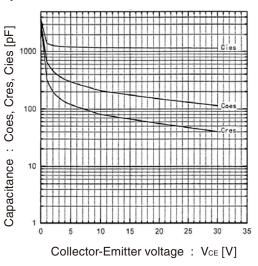
Reverse Biased Safe Operating Area +V_{GE}=15V, -V_{GE} \leq 15V, Tj=125°C, RG \geq 16\Omega



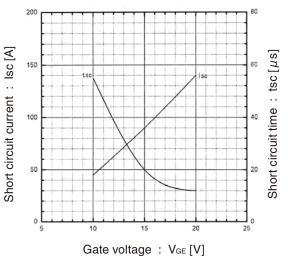




Capacitance vs. Collector-Emitter voltage $Tj=25^{\circ}C$

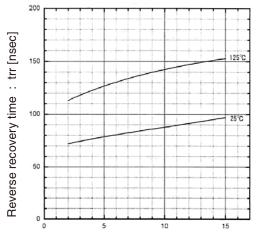


Typical short circuit capability Vcc=800V, RG=16Ω, Tj=125°C



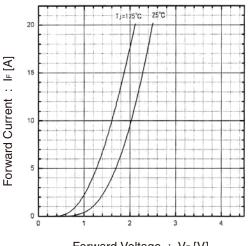
Characteristics

Reverse recovery time vs. Forward current VR=200V, -di/dt=100A/ μ sec



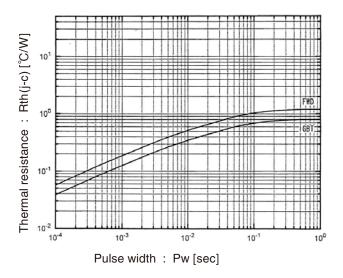
Forward current : IF [A]

Forward voltage vs. Forward current

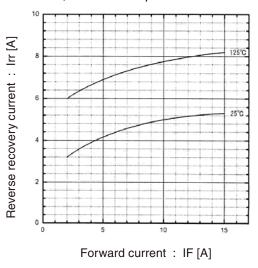


Forward Voltage : $V_F[V]$

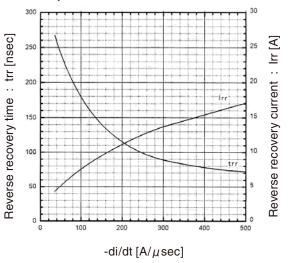
Transient thermal resistance



Reverse recovery current vs. Forward current VR=200V, -di/dt=100A/ μ sec



Reverse recovery chracteristics vs. -di/dt IF=10A, Tj=125°C



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